

PW2321

20V P-Channel MOSFET

-4A -20V; $R_{DS(ON)typ}=35m\Omega@-4.5V$, $R_{DS(ON)typ}=49m\Omega@-2.5V$,
 $R_{DS(ON)typ}=74m\Omega@-1.8V$

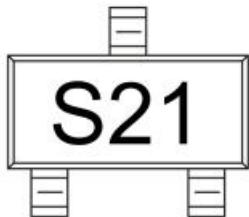
FEATURE

- TrenchFET Power MOSFET

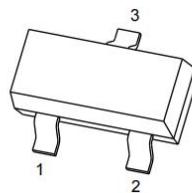
Application

- PA Switch
- Load Switch

MARKING:

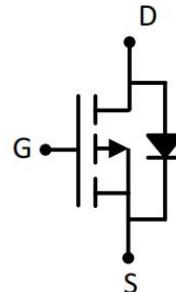


SOT-23



1. GATE
2. SOURCE
3. DRAIN

Schematic diagram



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	-4	A
Pulsed Drain Current	I_{DM}	-12	A
Continuous Drain Current	I_S	-0.59	A
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^\circ C/W$
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{STG}	-55~+150	$^\circ C$

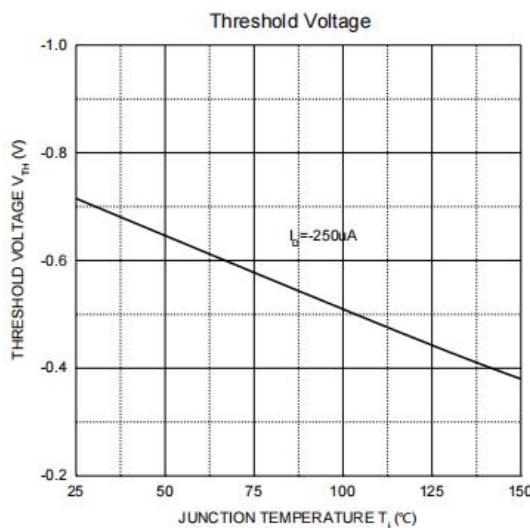
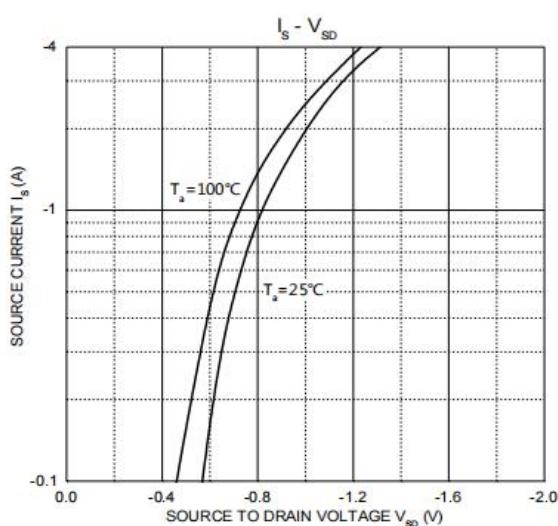
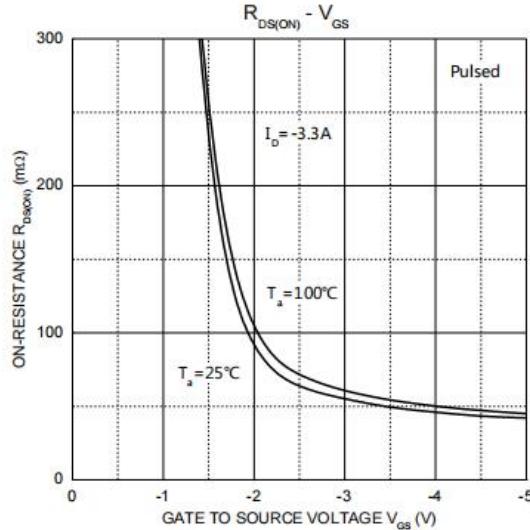
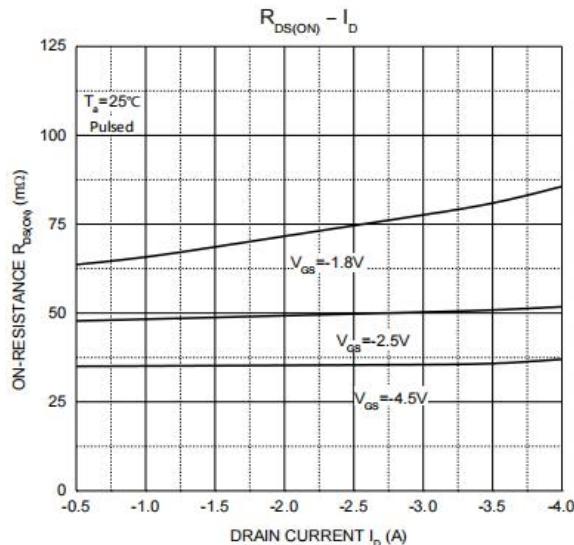
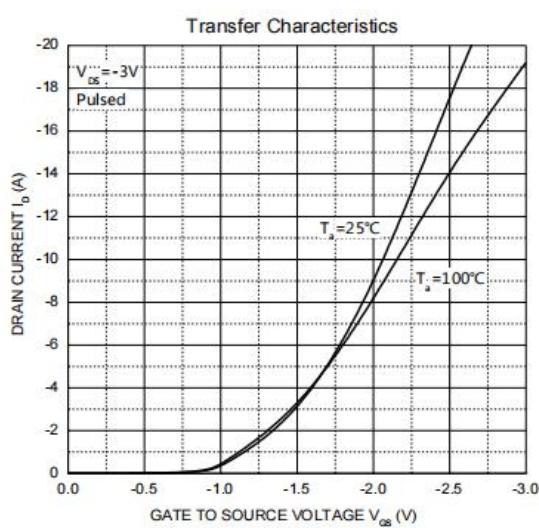
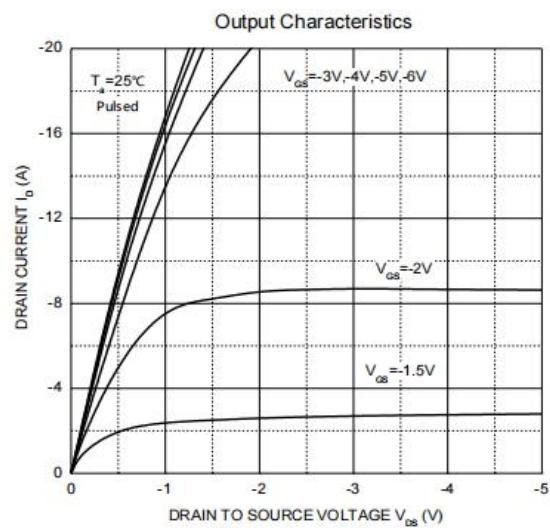
MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = -250\mu\text{A}$	-20			V
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = -16\text{V}, V_{\text{GS}} = 0\text{V}$			-1	μA
Gate-body leakage current	I_{GSS}	$V_{\text{GS}} = \pm 12\text{V}, V_{\text{DS}} = 0\text{V}$			± 100	nA
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = -250\mu\text{A}$	-0.4	-0.7	-1	V
Drain-source on-resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = -4.5\text{V}, I_D = -3.3\text{A}$		35	45	$\text{m}\Omega$
		$V_{\text{GS}} = -2.5\text{V}, I_D = -2.8\text{A}$		49	65	
		$V_{\text{GS}} = -1.8\text{V}, I_D = -2.3\text{A}$		74	110	
Forward transconductance	g_{FS}	$V_{\text{DS}} = -5\text{V}, I_D = -3.3\text{A}$	3			S
Dynamic characteristics						
Input Capacitance ^(a,b)	C_{iss}	$V_{\text{DS}} = -6\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		715		pF
Output Capacitance ^(a,b)	C_{oss}			170		
Reverse Transfer Capacitance ^(a,b)	C_{rss}			120		
Total gate charge ^(a)	Q_g	$V_{\text{DS}} = -6\text{V}, V_{\text{GS}} = -4.5\text{V}, I_D = -3.3\text{A}$			13	nC
Gate-source charge ^(a)	Q_{gs}				1.2	
Gate-drain charge ^(a)	Q_{gd}				1.6	
Switching^(a,b)						
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = -6\text{V}, V_{\text{GEN}} = -4.5\text{V}, I_D = -1.0\text{A}, R_L = 6\Omega, R_G = 6\Omega$			25	ns
Turn-on rise time	t_r				55	
Turn-off delay time	$t_{\text{d}(\text{off})}$				90	
Turn-off fall time	t_f				60	
Source-Drain Diode characteristics						
Diode Forward voltage	V_{DS}	$I_S = -1.6\text{A}, V_{\text{GS}} = 0\text{V}$			-1.2	V

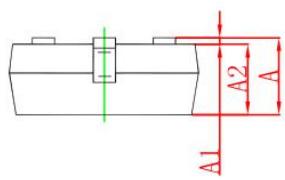
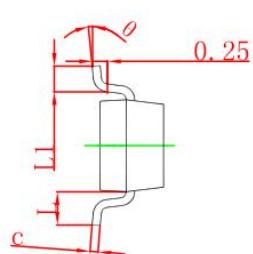
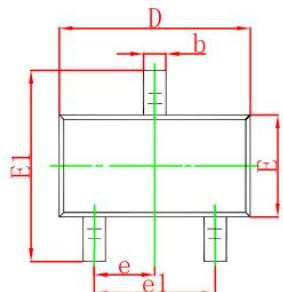
Notes:

- a. Pulse Test ;Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
b. These parameters have no way to verify.

Typical Electrical and Thermal Characteristics



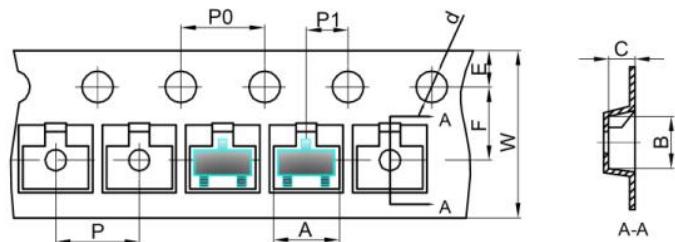
SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

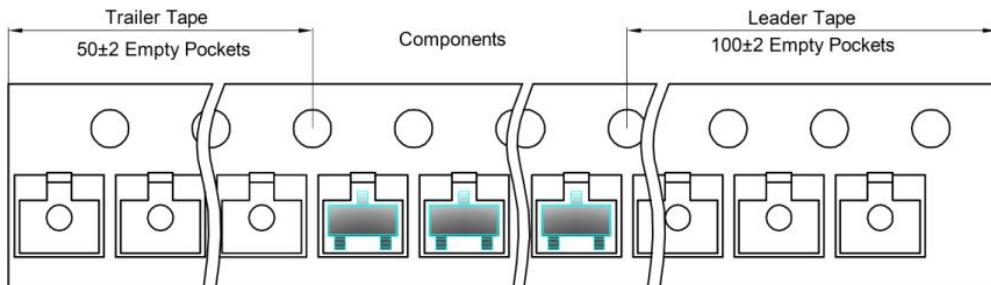
SOT-23 Tape and Reel

SOT-23 Embossed Carrier Tape

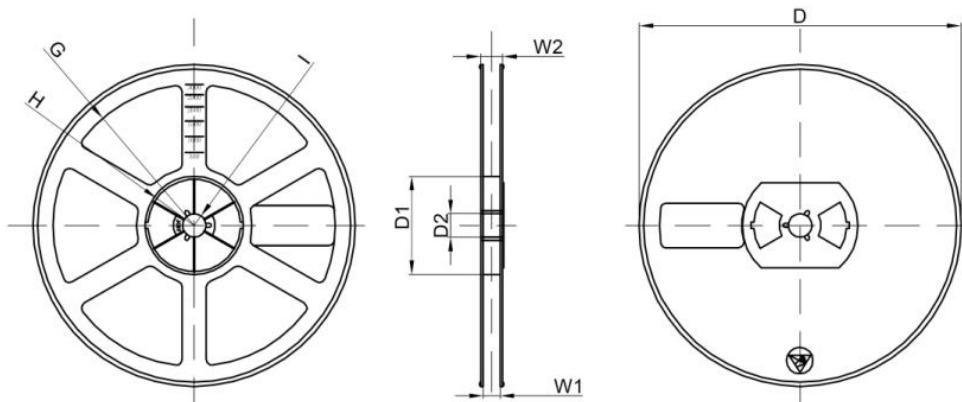


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer



SOT-23 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	